

isc Silicon NPN Power Transistor

2SC4370

DESCRIPTION

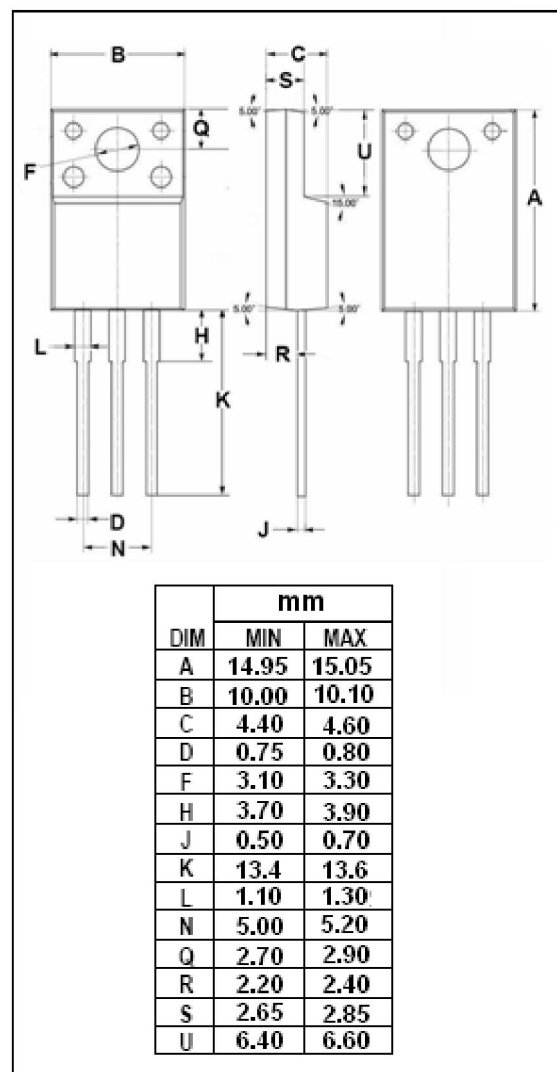
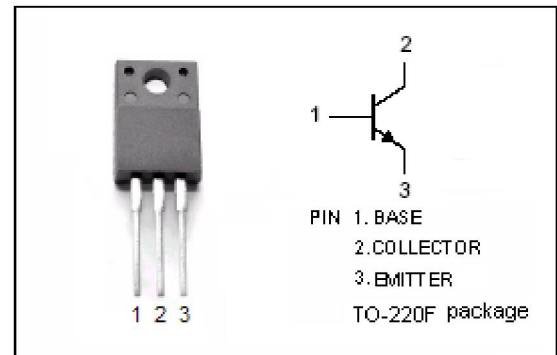
- High Collector-Emitter Breakdown Voltage
V_{CEO}= 160V(Min)
- Complement to Type 2SA1659
- Full-mold package that does not require an insulating board or bushing when mounting.

APPLICATIONS

- Designed for high voltage applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	160	V
V _{CEO}	Collector-Emitter Voltage	160	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _{C(DC)}	Collector Current(DC)	1.5	A
I _{B(DC)}	Base Current	0.15	A
P _C	Collector Power Dissipation @T _C =25°C	20	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



isc Silicon NPN Power Transistor**2SC4370****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA ; I _B = 0	160			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 500mA; I _B = 50mA			1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 500mA ; V _{CE} = 5V			1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 160V ; I _E = 0			1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C =0			1.0	μ A
h _{FE}	DC Current Gain	I _C = 100mA ; V _{CE} = 5V	70		240	
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V;f= 1.0MHz		25		pF
f _T	Current-Gain—Bandwidth Product	I _C = 100m A ; V _{CE} = 10V		100		MHz

◆ **h_{FE} Classifications**

O	Y
70-140	120-240